

Schottky Diode

$$V_{RRM} = 45\text{ V}$$

$$I_{FAV} = 2 \times 30\text{ A}$$

$$V_F = 0.45\text{ V}$$

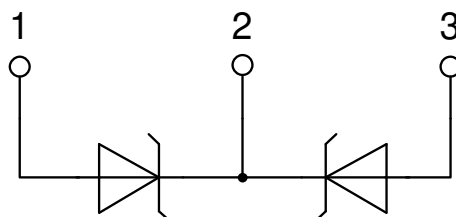
High Performance Schottky Diode
 Low Loss and Soft Recovery
 Common Cathode

Part number

DSSK60-0045B



Backside: cathode



Features / Advantages:

- Very low V_f
- Extremely low switching losses
- Low I_{rm} values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				45	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				45	V
I_R	reverse current, drain current	$V_R = 45\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			40	mA
		$V_R = 45\text{ V}$	$T_{VJ} = 100^{\circ}\text{C}$			200	mA
V_F	forward voltage drop	$I_F = 30\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			0.50	V
		$I_F = 60\text{ A}$				0.68	V
		$I_F = 30\text{ A}$	$T_{VJ} = 125^{\circ}\text{C}$			0.45	V
		$I_F = 60\text{ A}$				0.66	V
I_{FAV}	average forward current	$T_C = 125^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}\text{C}$			30	A
V_{F0}	threshold voltage	} for power loss calculation only		$T_{VJ} = 150^{\circ}\text{C}$		0.24	V
r_F	slope resistance					6.5	mΩ
R_{thJC}	thermal resistance junction to case					1.1	K/W
R_{thCH}	thermal resistance case to heatsink				0.25		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				115	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}\text{C}$			640	A
C_J	junction capacitance	$V_R = 5\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		1.94		nF
E_{AS}	non-repetitive avalanche energy	$I_{AS} = 28\text{ A}$ $L = 180\text{ }\mu\text{H}$	$T_{VJ} = 25^{\circ}\text{C}$			112	mJ
I_{AR}	repetitive avalanche current	$V_A = 1.5 \cdot V_R$ typ. $f = 10\text{ kHz}$				2.8	A

Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾			70	A
T_{VJ}	virtual junction temperature		-55		150	°C
T_{op}	operation temperature		-55		125	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0.8		1.2	Nm
F_C	mounting force with clip		20		120	N

Product Marking

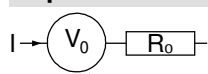


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSSK60-0045B	DSSK60-0045B	Tube	30	501501

Equivalent Circuits for Simulation

^{*} on die level

$T_{VJ} = 150^{\circ}\text{C}$



Schottky

$V_{0\max}$ threshold voltage 0.24

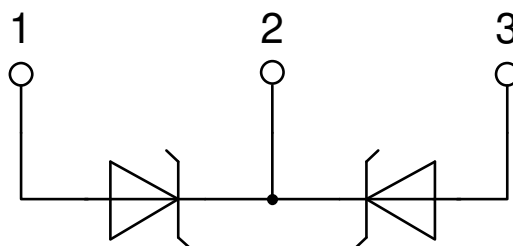
V

$R_{0\max}$ slope resistance ^{*} 4

mΩ

Outlines TO-247


Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215	BSC	5.46	BSC
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242	BSC	6.14	BSC
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



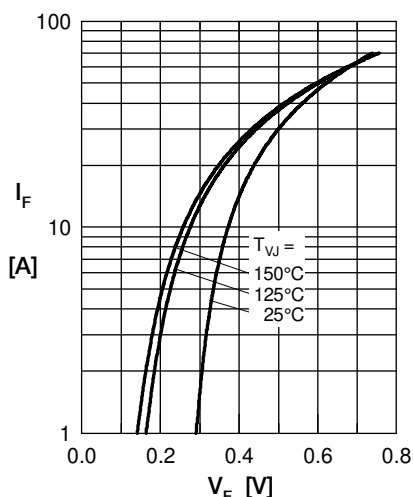
Schottky


Fig. 1 Max. forward voltage drop characteristics

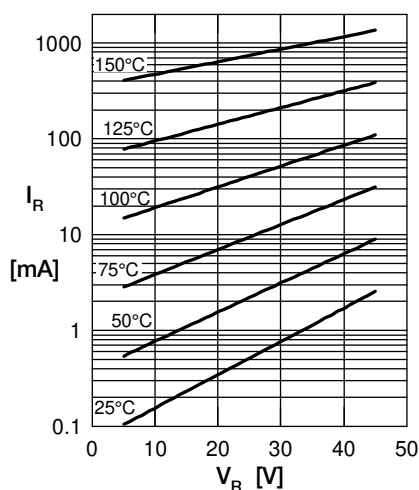
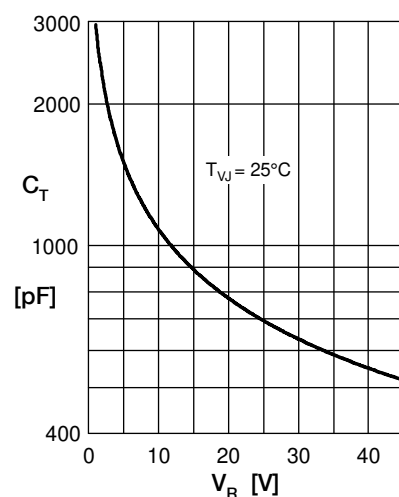
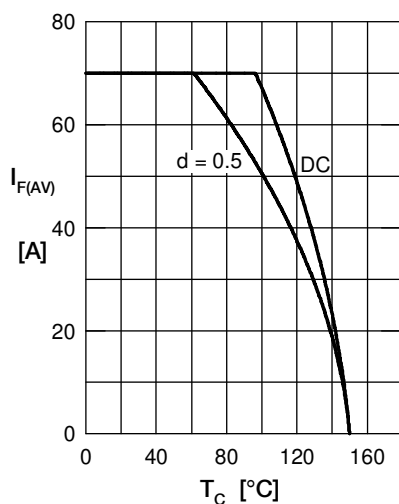
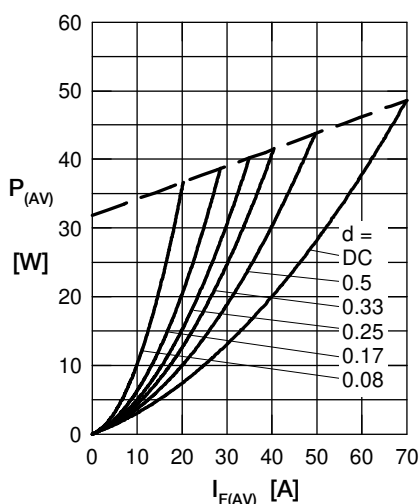

 Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

 Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

 Fig. 4 Average forward current $I_{F(AV)}$ vs. case temp. T_C


Fig. 5 Forward power loss characteristics

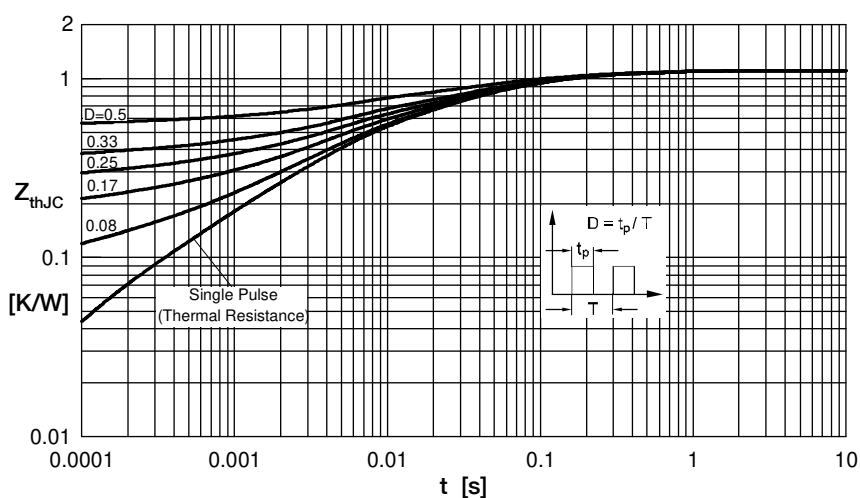


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode